

HT-02-026



November 18, 2003

To: Commissioner for Patents
P.O.Box 1450
Alexandria, VA 22313-1450

Fr: George O. Saile, Reg. No. 19,572
28 Davis Avenue
Poughkeepsie, N.Y. 12603

Subject:

Serial No. 10/647,718 08/25/03

Yimin Guo

MAGNETIC MEMORY WITH SELF-ALIGNED
MAGNETIC KEEPER STRUCTURE

Grp. Art Unit:

INFORMATION DISCLOSURE STATEMENT

Enclosed is Form PTO-1449, Information Disclosure Citation
In An Application.

The following Patents and/or Publications are submitted to
comply with the duty of disclosure under CFR 1.97-1.99 and
37 CFR 1.56. Copies of each document is included herewith.

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being
deposited with the United States Postal Service as first class
mail in an envelope addressed to: Commissioner for Patents,
P.O. Box 1450, Alexandria, VA 22313-1450, on November 21, 2003.

Stephen B. Ackerman, Reg.# 37761

Signature/Date SB. Ackerman 11/21/03

U.S. Patent Application Publication US 2002/0055190 A1 to Anthony, "Magnetic Memory With Structures that Prevent Disruptions to Magnetization in Sense Layer," provides a keeper structure which is a soft magnetic material surrounding a current carrying conductor beneath the sense layer.

U.S. Patent 6,358,757 to Anthony, "Method for Forming Magnetic Memory With Structures that Prevent Disruptions to Magnetization in Sense Layers," provides a method for forming an array of MRAM devices at the intersections of orthogonally crossing upper and lower conductors in which the lower conductors are surrounded by soft magnetic keeper layers.

U.S. Patent 6,413,788 to Tuttle, "Keepers for MRAM Electrodes," within a variety of embodiments, teaches methods for forming keeper structures around both upper and lower conductors in damascene type trench configurations.

U.S. Patent 6,417,561 to Tuttle, "Keepers for MRAM Electrodes," discloses a magnetic memory device and method wherein a bit region sensitive to magnetic fields and preferably comprising a tunneling magnetoresistance (TMR) structure is located between a top electrode with a magnetic keeper and a bottom electrode with a magnetic keeper.

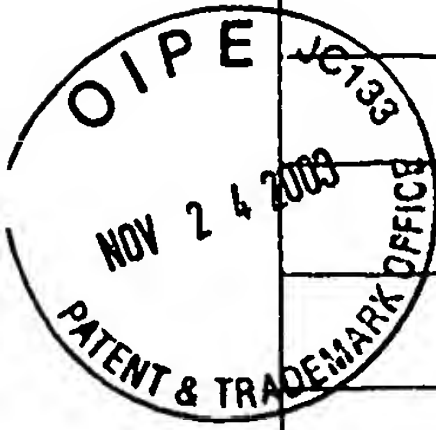
Sincerely,


Stephen B. Ackerman, Reg. #37761

Form PTO-1449 INFORMATION DISCLOSURE CITATION IN AN APPLICATION (Use several sheets if necessary)	Docket Number (Optional) HT-02-026	Application Number 10/647,718
	Applicant Yimin Guo	
	Filing Date 08/25/03	Group Art Unit

U. S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILED DATE IF APPROPRIATE
	6358757	3/19/02	Anthony	438	3	4/3/01
	6413788	7/2/02	Tuttle	438	3	2/28/01
	6417561	7/9/02	Tuttle	257	659	7/27/01



FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						YES	NO

OTHER DOCUMENTS (Including Author, Title, Date, Portion of Pages, Etc.)

	U.S. Patent Application Publication US 2002/0055190 A1
	to Anthony, "Magnetic Memory with Structures
	that Prevent Disruptions to Magnetization in Sense
	Layer", Pub Date 5/9/02, US Class 438/3.

EXAMINER	DATE CONSIDERED
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EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.